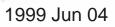
DATA SHEET

INTEGRATED CIRCUITS

UAA2068AHL Transmit chain and synthesizer with integrated VCO for DECT

Product specification File under Integrated Circuits, IC17









UAA2068AHL

FEATURES

- Economical integrated solution for frequency generation in DECT cordless telephones
- Integrated low phase noise 950 MHz VCO with frequency doubler
- Local Oscillator (LO) drive (–14 dBm) for RF mixer circuit
- Dedicated DECT PLL synthesizer
- 3-line serial interface bus
- · 3 dBm output preamplifier with an integrated switch
- Low current consumption from 3 V supply
- Compatible with Philips Semiconductors ABC baseband chip (PCD509x series).

APPLICATIONS

• 1880 to 1920 MHz DECT cordless telephones.

GENERAL DESCRIPTION

The UAA2068AHL BiCMOS device integrates a 950 MHz VCO, a frequency doubler, main and reference dividers and a phase comparator, to implement a phase-locked loop for DECT channel frequencies. The 1.9 GHz signal is buffered and switched, in TX mode, to drive the transmit power amplifier (CGY20xx series) or, in RX mode, to be used as an LO signal for the receiver mixer IC (UAA3540TS).

The synthesizer's main divider is driven by the frequency doubler output in the range from 1880 to 1920 MHz and programmed via a 3-wire serial bus.

The reference divider ratio is fixed at 16. Outputs of the main and reference dividers drive a phase comparator where a charge pump produces phase error current pulses for integration in an external loop filter. Only a passive loop filter is necessary. The charge-pump current (phase comparator gain) is set by an external resistor (R_{SET}) at pin R_{SET} .

The VCO is powered from an internally regulated voltage source and includes internal varicap diodes. Its tuning range is wider than the required band to allow for production spreads. In a Time Division Multiple Access (TDMA) system such as DECT, the VCO and the synthesizer are switched on one slot before the required one to lock the VCO to the required channel frequency. Just before the required slot, the synthesizer is switched off, allowing open-loop modulation of the VCO during transmission. When opening the loop, the frequency pulling (due to switching off the synthesizer) can be maintained within the DECT specification.

The device is designed to operate from 3 NiCd cells in pocket phones, with low current and nominal 3.6 V supplies. Separate power and ground pins are provided to the different parts of the circuit. The ground leads should be short-circuited externally to prevent large currents flowing across the die and thus causing damage. All supply pins (V_{CC}) must also be at the same potential, except V_{CC(CP)} which can be equal to or greater than the other supply pins (e.g. V_{CC} = 3 V and V_{CC(CP)} = 5 V for wider VCO control voltage range).

ORDERING INFORMATION

		PACKAGE	
	NAME	DESCRIPTION	VERSION
UAA2068AHL	LQFP32	plastic low profile quad flat package; 32 leads; body $5 \times 5 \times 1.4$ mm	SOT401-1

UAA2068AHL

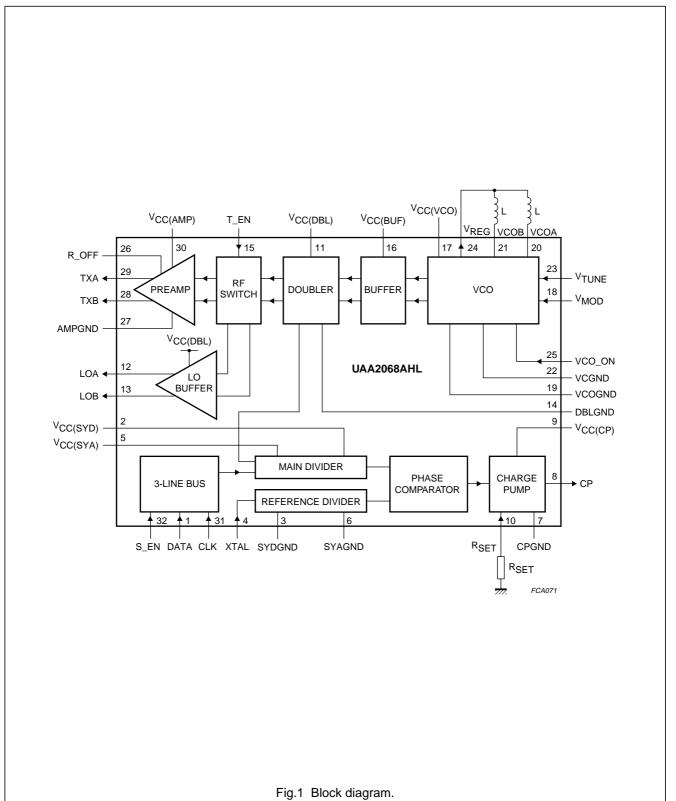
QUICK REFERENCE DATA

 V_{CC} = 3.6 V; $V_{CC(CP)}$ = 3.6 V; T_{amb} = 25 °C; unless otherwise specified. Characteristics for which only a typical value is given are not tested.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{CC}	supply voltage		3.0	3.6	5.2	V
V _{CC(CP)}	charge-pump supply voltage	$V_{CC(CP)} \ge V_{CC}$	3.0	3.6	5.2	V
I _{CC(SYA)} + I _{CC(SYD)}	synthesizer supply current	S_EN = 1	-	9.5	14	mA
I _{CC(VCO)} + I _{CC(BUF)}	VCO and buffer parts supply current	VCO_ON = 1	-	9.5	14	mA
I _{CC(DBL)}	doubler supply current	in RX mode	-	14.4	19	mA
		in TX mode	-	10	14	mA
I _{CC(AMP)}	TX preamplifier supply current	in RX mode	-	0	50	μA
		in TX mode	-	24	32	mA
I _{CC(pd)}	total supply current in Power-down mode		-	5	50	μA
f _{o(RF)}	RF output frequency		1880	-	1920	MHz
f _{xtal}	crystal reference input frequency		-	13.824	-	MHz
f _{PC}	phase comparator frequency		-	864	-	kHz
T _{amb}	operating ambient temperature		-10	-	+60	°C

UAA2068AHL

BLOCK DIAGRAM



UAA2068AHL

Product specification

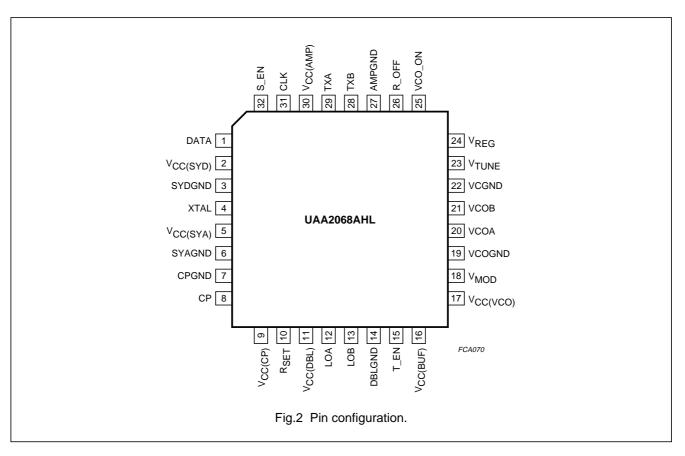
PINNING

SYMBOL	PIN	DESCRIPTION
DATA	1	3-wire programming bus data input
V _{CC(SYD)}	2	synthesizer CMOS divider positive supply voltage
SYDGND	3	synthesizer CMOS divider ground
XTAL	4	reference frequency input
V _{CC(SYA)}	5	synthesizer prescaler positive supply voltage
SYAGND	6	synthesizer prescaler ground
CPGND	7	charge-pump ground
СР	8	charge-pump output signal
V _{CC(CP)}	9	charge-pump positive supply voltage
R _{SET}	10	charge-pump current setting input
V _{CC(DBL)}	11	doubler positive supply voltage
LOA	12	local oscillator output A
LOB	13	local oscillator output B
DBLGND	14	doubler ground
T_EN	15	transmit enable signal input
V _{CC(BUF)}	16	VCO isolation buffer positive supply voltage
V _{CC(VCO)}	17	VCO positive supply voltage
V _{MOD}	18	transmit modulation input
VCOGND	19	VCO ground; note 1
VCOA	20	VCO inductor connection A
VCOB	21	VCO inductor connection B
VCGND	22	internal varicap ground; note 1
V _{TUNE}	23	VCO tuning input
V _{REG}	24	VCO regulator output
VCO_ON	25	VCO power-on control input; note 2
R_OFF	26	power-on control for RX LO buffer/TX preamplifier; note 3
AMPGND	27	transmit amplifier ground
ТХВ	28	transmit amplifier output B
TXA	29	transmit amplifier output A
V _{CC(AMP)}	30	transmit amplifier positive supply voltage
CLK	31	3-wire programming bus clock input
S_EN	32	synthesizer enable signal input

Notes

- 1. Pins 19 and 22 are internally short-circuited.
- 2. Use with S_PWR on ABC baseband chip.
- 3. Use with R_PWR on ABC baseband chip.

UAA2068AHL



FUNCTIONAL DESCRIPTION

Transmit chain

VCO, BUFFER AND FREQUENCY DOUBLER

The VCO operates at a nominal centre frequency of 950 MHz. The VCO is fully integrated apart from two inductors which complete the resonator network. The VCO operates from an on-chip regulated power supply (V_{REG}), which minimizes frequency disturbances due to variations in supply voltage. The buffered VCO signal is fed into a frequency doubler. The large difference between the transmitted and VCO frequencies reduces transmitter oscillator coupling problems.

The output of the doubler is used to drive the synthesizer main divider and can also be switched to either the TX preamplifier or the RX LO output buffer. The high isolation obtained from the VCO buffer and the frequency doubler ensures that very small frequency changes occur when turning on the TX preamplifier or the RX LO output buffer. In TX mode, the oscillator can be directly modulated with GMSK filtered data at pin V_{MOD} .

RF SWITCH

The RF switch passes the doubled VCO signal to either the TX preamplifier (when T_EN is HIGH) or to the RX LO buffer (when T_EN is LOW). In TX mode, the difference in the RF power levels, observed at the TX output when T_EN is switched from LOW-to-HIGH, is typically 40 dB.

TX PREAMPLIFIER

The TX preamplifier amplifies the RF signal up to a level of 3 dBm which is suitable for use with Philips Semiconductors DECT power amplifiers such as the CGY20xx series. It is powered-up when both R_OFF and VCO_ON are HIGH.

RX LO BUFFER

The RX LO buffer outputs the frequency doubled VCO signal at a level of -14 dBm. This signal can then be used as the local oscillator drive for the receive mixers of devices such as the UAA3540TS. The buffer is powered-up when R_OFF is LOW and VCO_ON is HIGH.

UAA2068AHL

Synthesizer

MAIN DIVIDER

The main divider is clocked by the RF signal from the internal frequency doubler. The divider operates at frequencies from 1880 to 1920 MHz. It consists of a bipolar prescaler followed by a CMOS counter. Any main divider ratio from 2176 to 2303 inclusive can be programmed.

REFERENCE DIVIDER

The reference divider is clocked by the signal at pin XTAL. The circuit operates with levels from 50 to 500 mV (RMS) at a frequency of 13.824 MHz, with a fixed divider ratio of 16.

PHASE COMPARATOR

The phase comparator is driven by the output of the main and reference dividers. It produces current pulses at the charge-pump output (pin CP). The pulse duration is equal to the difference in time of arrival of the edges from the two dividers. If the main divider edge arrives first, pin CP sinks current; if the reference divider edge arrives first, pin CP sources current. The DC value of the charge-pump current is nominally ten times the current drawn by the external resistor connected to pin R_{SET} Additional circuitry is included to ensure that the gain of the phase detector remains linear even for small phase errors.

The charge pump has a separate supply, $V_{CC(CP)}$, which helps to reduce the interference on the charge-pump output from other parts of the circuit. $V_{CC(CP)}$ can be higher than the other supply voltages if a wider range on the VCO input is required. The $V_{CC(CP)}$ voltage must not be less than that on other V_{CC} pins.

Serial programming bus

A simple 3-line unidirectional serial bus is used to program the circuit. These 3 lines are data (DATA), clock (CLK) and enable (S_EN). The data sent to the device is loaded in bursts framed by S_EN. Programming clock edges and their appropriate data bits are ignored until S_EN goes active LOW. The programmed information is read directly by the main divider when S_EN returns HIGH. During synthesizer operation, S_EN should be kept HIGH. In normal operating mode, the last 16 bits serially clocked into the device are retained within the register. Additional leading bits are ignored, and no check is made on the number of clock pulses. The data format is given in Table 2. The first bit entered is b15, the last bit is b0. For the divider ratio, the first bit (b6) entered is the most significant (MSB).

S_EN must be LOW to capture new programming data. S_EN must be HIGH to switch-on the synthesizer.

Operating modes

The synthesizer is on when the input signal S_EN is HIGH, and off when S_EN is LOW. When turned on, the dividers and phase detector are synchronized to avoid a random initial phase error. When turned off, the phase detector is synchronized with the dividers to avoid interrupting a charge-pump pulse.

The VCO is on when the input signal VCO_ON is HIGH. The polarity of VCO_ON is chosen for compatibility with output S_PWR at the ABC chip. When turned on, it needs some time (typically 30 μ s) to reach its steady state.

The TX preamplifier is on when both R_OFF and VCO_ON are HIGH. The polarity of R_OFF is chosen for compatibility with output R_PWR at the ABC chip. When turned on, it needs some time (typically 10 μ s) to reach its steady state. In transmit mode, the timing of the R_OFF LOW-to-HIGH transition can be chosen such that the TX preamplifier is turned on while the synthesizer loop remains closed thus avoiding frequency pulling of the VCO. In the receive mode, depending on the exact timing of R_OFF compared to VCO_ON, the TX preamplifier can be switched on at the beginning of the previous slot, but is switched off when R_OFF goes LOW; this occurs when the synthesizer loop is closed. The LO output amplifier is turned on when R_OFF is LOW and VCO_ON is HIGH.

The UAA2068AHL has a very low current consumption in Power-down mode.

UAA2068AHL

Product specification

BLOCK STATUS	VCO_ON	R_OFF	T_EN	S_EN
VCO, buffer, doubler, RF switch, TX preamplifier and LO buffer powered-down	0	Х	Х	Х
VCO, buffer, doubler, RF switch and TX preamplifier powered-up	1	1	1	Х
LO buffer powered-down				
Nominal RF signal at TX output				
VCO, buffer, doubler, RF switch and TX preamplifier powered-up	1	1	0	Х
LO buffer powered-down				
No RF signal output				
VCO, buffer, doubler, RF switch and LO buffer powered-up	1	0	0	Х
TX preamplifier powered-down				
Nominal RF signal at LO buffer output				
VCO, buffer, doubler, RF switch and LO buffer powered-up	1	0	1	Х
TX preamplifier powered-down				
No RF signal output				
To power-down PLL blocks; notes 2 and 3	1	Х	Х	0
To power-up PLL blocks; notes 2 and 3	1	Х	Х	1
All blocks in power-down state; notes 2 and 3	0	Х	Х	0
New PLL division ratio is loaded and the PLL blocks are powered-up on the rising edge of S_EN; note 3	1	Х	Х	0 to 1

Table 1Mode control; note 1

Notes

- 1. X = don't care.
- 2. PLL blocks are the main divider, reference divider, phase detector and charge pump.
- 3. A reference signal is needed on pin XTAL for correct operation.

Table 2Bit allocation; note 1

FIRST IN	FIRST IN REGISTER BIT ALLOCATION									LAST IN					
							DATA	FIELD							
b15	b14	b13	b12	b11	b10	b9	b8	b7	b6 ⁽²⁾	b5	b4	b3	b2	b1	b0
0	0	0	1	0	0	0	0	1		n	nain div	vider pr	ogramr	ning ⁽³⁾	

Notes

- 1. For normal operation, b15 to b0 need to be programmed.
- 2. Bit b6 is the MSB of the main divider coefficient.
- 3. The main divider ratio is equal to 2176 plus the programmed value (see Table 3).

UAA2068AHL

Table 3 Main divider programming

b6	b5	b4	b3	b2	b1	b0	MAIN DIVIDER RATIO	SYNTHESIZED FREQUENCY (MHz)
		Binary	/ equivale	nt of n			2176 + n	0.864 × (2176 + n)
0	0	0	0	0	0	1	2177	1880.928
0	0	1	0	1	0	1	2197	1898.208

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	supply voltage		-0.3	+5.5	V
V _{CC(CP)}	charge-pump supply voltage		-0.3	+5.5	V
$V_{CC(CP)} - V_{CC}$	difference in voltage between $V_{CC(CP)}$ and V_{CC}		-0.3	+5.5	V
ΔGND	difference in ground supply voltage applied between all ground pins	note 1	-	0.3	V
P _{tot}	total power dissipation		-	275	mW
T _{stg}	storage temperature		-55	+125	°C
T _{amb}	operating ambient temperature		-10	+60	°C
Tj	junction temperature		-	150	°C

Note

1. Pins short-circuited internally must be short-circuited externally.

HANDLING

Inputs and outputs are protected against electrostatic discharge in normal handling. However, to be totally safe, it is desirable to take normal precautions appropriate to handling MOS devices.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	100	K/W

UAA2068AHL

CHARACTERISTICS

 V_{CC} = 3.6 V; $V_{CC(CP)}$ = 3.6 V; T_{amb} = 25 °C; unless otherwise specified. Characteristics for which only a typical value is given are not tested.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Supplies					-	•
V _{CC}	supply voltage		3	3.6	5.2	V
V _{CC(CP)}	charge-pump supply voltage	$V_{CC(CP)} \ge V_{CC}$	3	3.6	5.2	V
I _{CC(SYA)} + I _{CC(SYD)}	synthesizer supply current	S_EN = 1	-	9.5	14	mA
I _{CC(VCO)} + I _{CC(BUF)}	VCO and buffer parts supply current	VCO_ON = 1	-	9.5	14	mA
I _{CC(DBL)}	doubler supply current	in RX mode	_	14.4	19	mA
		in TX mode	_	10	14	mA
I _{CC(AMP)}	TX preamplifier supply current	in RX mode	-	0	50	μA
		in TX mode	_	24	32	mA
I _{CC(pd)}	total supply current in Power-down mode		-	5	50	μA
Synthesiz	er main divider					
f _{RF}	RF frequency		1880	-	1920	MHz
R _m	main divider ratio		2176	_	2303	
Synthesiz	er reference divider input		I			-
f _{xtal}	crystal reference input frequency		-	13.824	-	MHz
V _{xtal(rms)}	sinusoidal input signal level (RMS value)		50	-	500	mV
R _{ref}	reference division ratio		-	16	-	
R _i	input resistance (real part of the input impedance)	f _{xtal} = 13.824 MHz	-	4.5	_	kΩ
Ci	input capacitance (imaginary part of the input impedance)		-	2.5	_	pF
Phase det	ector			ŀ		
f _{PC}	phase comparator frequency		_	864	_	kHz
Charge-pu	Imp output	,	I			
I _{o(cp)}	charge-pump output current	$V_{CP} = 0.5 V_{CC};$ $R_{SET} = 8.2 \text{ k}\Omega$	-	1.5	-	mA
I _{o(cp)(err)}	charge-pump output current error	note 1	-25	_	+25	%
Imatch	sink-to-source current matching	$V_{CP} = 0.5 V_{CC}$	_	±5	-	%
I _{L(cp)}	charge-pump-off leakage current	$V_{CP} = 0.5 V_{CC}$	-1	0	+1	nA
	imp current setting resistor input	; pin R _{SET}				
R _{SET}	external resistor connected between pin R _{SET} and ground		5.6	-	12	kΩ
V _{SET}	regulated voltage at pin R _{SET}		_	1.2	_	V

UAA2068AHL

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
vco			1		-	
f _{VCO}	oscillator frequency	over full temperature range; note 2	940	-	960	MHz
G _{VCO}	tuning input VCO gain		_	45	-	MHz/V
G _{MOD}	modulation input VCO gain		-	1	-	MHz/V
Switch pa	rt					
FTLO _{TXoff}	isolation between LO and TX outputs when TX preamplifier is off (RX mode)	f = 1890 MHz; note 2	-	-50	-	dB
FTLO _{TXon}	isolation due to the switch when TX preamplifier is on (TX mode)	f = 1890 MHz; note 2	-	-40	-	dB
TX pream	olifier and LO buffer parts					
P _{o(TX)}	TX preamplifier output power	over full temperature range; note 2	0	3	7	dBm
f _{o(TX)}	output frequency on TX preamplifier or LO buffer		1880	_	1920	MHz
R _{o(TX)}	TX preamplifier output resistance (real part of the parallel output impedance)	balanced	_	150	_	Ω
C _{o(TX)}	TX preamplifier output capacitance (imaginary part of the parallel output impedance)	balanced	-	0.5	-	pF
FTVCO _{TX}	VCO frequency feedthrough at the TX output	referenced to the f _{o(TX)} level; note 2	-	-41	-36	dBc
CNR ₂₅	carrier-to-noise ratio at TX output	carrier offset ∆f = 25 kHz	-	-75	-	dBc/Hz
CNR ₄₆₈₆	carrier-to-noise ratio at TX output	carrier offset ∆f = 4686 kHz	-	-135	-132	dBc/Hz
$\Delta f_{o(offset)}$	total frequency shift due to 200 mV V _{CC} change disabling the synthesizer	measured 20 μs after disabling the synthesizer; note 2	-	-	±15	kHz
$\Delta f_{o(drift)}$	frequency drift during a slot	note 2	_	1	± 10	kHz
P _{o(LO)}	LO preamplifier output power	note 2	-	-14	-	dBm
R _{o(LO)}	LO preamplifier output resistance (real part of the parallel output impedance)	balanced	_	120	_	Ω

UAA2068AHL

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT			
C _{o(LO)}	LO preamplifier output capacitance (imaginary part of the parallel output impedance)	balanced	-	0	-	pF			
Interface I	Interface logic input signal levels; pins DATA, CLK, S_EN, T_EN, R_OFF and VCO_ON								
V _{IH}	HIGH-level input voltage	note 3	2.2	_	V _{CC} + 0.3	V			
V _{IL}	LOW-level input voltage		-0.3	_	+0.5	V			
I _{bias}	input bias current	logic 1 or logic 0	-5	_	+5	μA			
Ci	input capacitance		_	2	_	pF			

Notes

1. Condition: $0.5 < V_{CP} < (V_{CC(CP)} - 0.5)$.

2. Measured and guaranteed only on the Philips evaluation board, including PCB and balun filter.

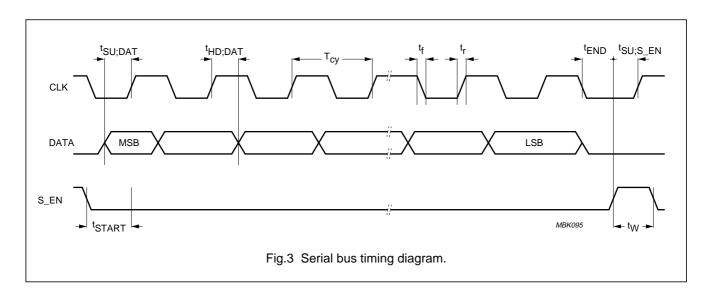
3. V_{IH} should never exceed 5.2 V.

SERIAL BUS TIMING CHARACTERISTICS

 V_{CC} = 3.6 V; T_{amb} = 25 °C; unless otherwise specified.

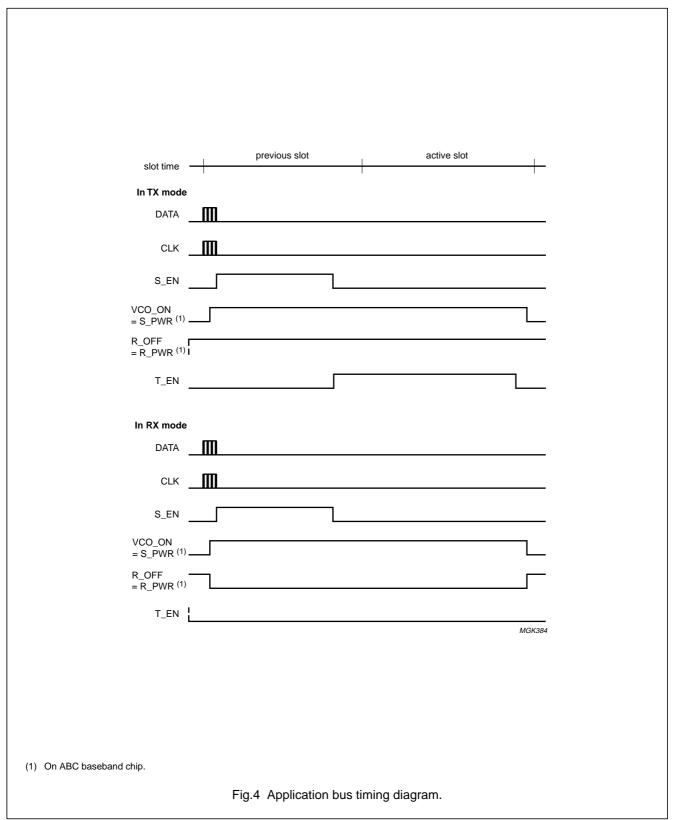
SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
Serial prog	gramming clock; CLK	I		-	
t _r	input rise time	-	10	40	ns
t _f	input fall time	_	10	40	ns
T _{cy}	clock period	100	-	-	ns
Enable pro	ogramming; S_EN				
t _{START}	delay to rising clock edge	40	_	-	ns
t _{END}	delay from last falling clock edge	-20	-	-	ns
t _W	minimum inactive pulse width	4000	-	-	ns
t _{SU;S_EN}	enable set-up time to next clock edge	20	-	-	ns
Register s	erial input data; DATA				
t _{SU;DAT}	input data to clock set-up time	20	_	-	ns
t _{HD;DAT}	input data to clock hold time	20	-	_	ns

UAA2068AHL



UAA2068AHL

TIMING CHARACTERISTICS



UAA2068AHL

APPLICATION INFORMATION

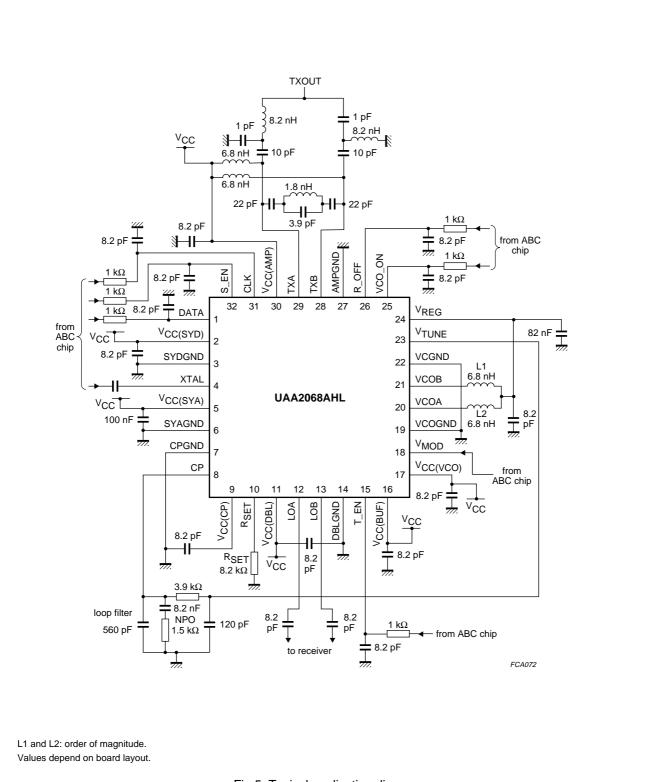
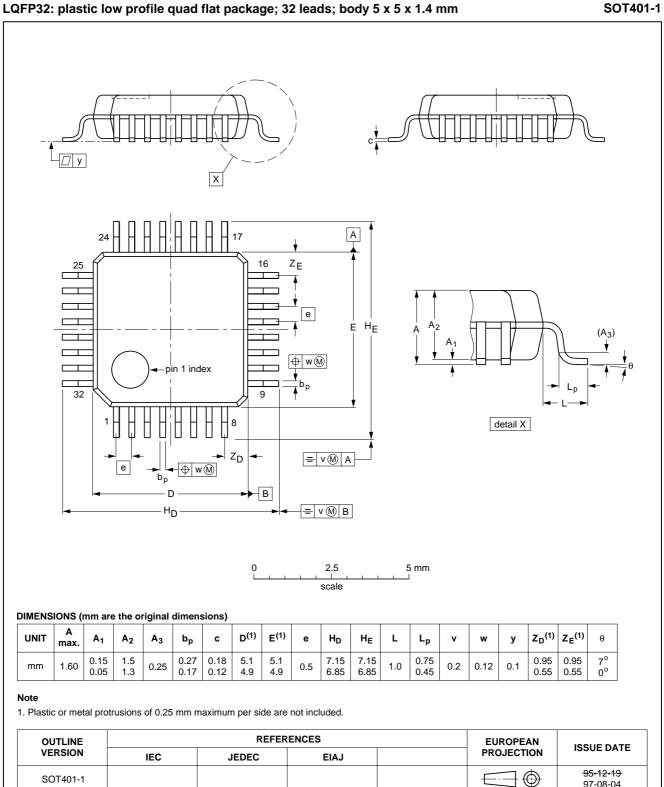


Fig.5 Typical application diagram.

PACKAGE OUTLINE



UAA2068AHL

97-08-04

UAA2068AHL

SOLDERING

Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering is not always suitable for surface mount ICs, or for printed-circuit boards with high population densities. In these situations reflow soldering is often used.

Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, infrared/convection heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 230 °C.

Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

• For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to $300 \,^{\circ}$ C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 $^\circ C.$

UAA2068AHL

Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE	SOLDERING METHOD	
	WAVE	REFLOW ⁽¹⁾
BGA, SQFP	not suitable	suitable
HLQFP, HSQFP, HSOP, SMS	not suitable ⁽²⁾	suitable
PLCC ⁽³⁾ , SO, SOJ	suitable	suitable
LQFP, QFP, TQFP	not recommended ⁽³⁾⁽⁴⁾	suitable
SSOP, TSSOP, VSO	not recommended ⁽⁵⁾	suitable

Notes

- 1. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the *"Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods"*.
- 2. These packages are not suitable for wave soldering as a solder joint between the printed-circuit board and heatsink (at bottom version) can not be achieved, and as solder may stick to the heatsink (on top version).
- 3. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 4. Wave soldering is only suitable for LQFP, TQFP and QFP packages with a pitch (e) equal to or larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- 5. Wave soldering is only suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
more of the limiting values r of the device at these or at a	accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or nay cause permanent damage to the device. These are stress ratings only and operation any other conditions above those given in the Characteristics sections of the specification imiting values for extended periods may affect device reliability.
Application information	
Where explication information	an is given, it is advisory and does not form part of the encodification

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

UAA2068AHL

NOTES

Philips Semiconductors – a worldwide company

Argentina: see South America Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113, Tel. +61 2 9805 4455, Fax. +61 2 9805 4466 Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213, Tel. +43 1 60 101 1248, Fax. +43 1 60 101 1210 Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6, 220050 MINSK, Tel. +375 172 20 0733, Fax. +375 172 20 0773 Belgium: see The Netherlands Brazil: see South America Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor, 51 James Bourchier Blvd., 1407 SOFIA Tel. +359 2 68 9211, Fax. +359 2 68 9102 Canada: PHILIPS SEMICONDUCTORS/COMPONENTS, Tel. +1 800 234 7381. Fax. +1 800 943 0087 China/Hong Kong: 501 Hong Kong Industrial Technology Centre, 72 Tat Chee Avenue, Kowloon Tong, HONG KONG, Tel. +852 2319 7888, Fax. +852 2319 7700 Colombia: see South America Czech Republic: see Austria Denmark: Sydhavnsgade 23, 1780 COPENHAGEN V, Tel. +45 33 29 3333, Fax. +45 33 29 3905 Finland: Sinikalliontie 3, FIN-02630 ESPOO, Tel. +358 9 615 800, Fax. +358 9 6158 0920 France: 51 Rue Carnot, BP317, 92156 SURESNES Cedex, Tel. +33 1 4099 6161, Fax. +33 1 4099 6427 Germany: Hammerbrookstraße 69, D-20097 HAMBURG, Tel. +49 40 2353 60, Fax. +49 40 2353 6300 Hungary: see Austria India: Philips INDIA Ltd, Band Box Building, 2nd floor, 254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025, Tel. +91 22 493 8541, Fax. +91 22 493 0966 Indonesia: PT Philips Development Corporation, Semiconductors Division, Gedung Philips, Jl. Buncit Raya Kav.99-100, JAKARTA 12510, Tel. +62 21 794 0040 ext. 2501, Fax. +62 21 794 0080 Ireland: Newstead, Clonskeagh, DUBLIN 14 Tel. +353 1 7640 000. Fax. +353 1 7640 200 Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053, TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007 Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3, 20124 MILANO, Tel. +39 02 67 52 2531, Fax. +39 02 67 52 2557 Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108-8507, Tel. +81 3 3740 5130, Fax. +81 3 3740 5057 Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL, Tel. +82 2 709 1412, Fax. +82 2 709 1415 Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR, Tel. +60 3 750 5214, Fax. +60 3 757 4880 Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905, Tel. +9-5 800 234 7381, Fax +9-5 800 943 0087 Middle East: see Italy

For all other countries apply to: Philips Semiconductors, International Marketing & Sales Communications, Building BE-p, P.O. Box 218, 5600 MD EINDHOVEN, The Netherlands, Fax. +31 40 27 24825

Tel. +31 40 27 82785, Fax. +31 40 27 88399 New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND, Tel. +64 9 849 4160, Fax. +64 9 849 7811 Norway: Box 1, Manglerud 0612, OSLO, Tel. +47 22 74 8000, Fax. +47 22 74 8341 Pakistan: see Singapore Philippines: Philips Semiconductors Philippines Inc.,

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,

106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI, Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474 **Poland:** UI. Lukiska 10, PL 04-123 WARSZAWA,

Tel. +48 22 612 2831, Fax. +48 22 612 2327 Portugal: see Spain

Romania: see Italy

Russia: Philips Russia, UI. Usatcheva 35A, 119048 MOSCOW, Tel. +7 095 755 6918, Fax. +7 095 755 6919

Singapore: Lorong 1, Toa Payoh, SINGAPORE 319762, Tel. +65 350 2538, Fax. +65 251 6500

Slovakia: see Austria

Slovenia: see Italy

South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale, 2092 JOHANNESBURG, P.O. Box 58088 Newville 2114, Tel. +27 11 471 5401, Fax. +27 11 471 5398

South America: Al. Vicente Pinzon, 173, 6th floor, 04547-130 SÃO PAULO, SP, Brazil,

Tel. +55 11 821 2333, Fax. +55 11 821 2382 Spain: Balmes 22, 08007 BARCELONA,

Tel. +34 93 301 6312, Fax. +34 93 301 4107

Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM,

Tel. +46 8 5985 2000, Fax. +46 8 5985 2745 **Switzerland:** Allmendstrasse 140, CH-8027 ZÜRICH, Tel. +41 1 488 2741 Fax. +41 1 488 3263

Taiwan: Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1, TAIPEI, Taiwan Tel. +886 2 2134 2886, Fax. +886 2 2134 2874

Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd., 209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260, Tel. +66 2 745 4090, Fax. +66 2 398 0793

Turkey: Yukari Dudullu, Org. San. Blg., 2.Cad. Nr. 28 81260 Umraniye, ISTANBUL, Tel. +90 216 522 1500, Fax. +90 216 522 1813

Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7, 252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes, MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421

United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409, Tel. +1 800 234 7381, Fax. +1 800 943 0087

Uruguay: see South America

Vietnam: see Singapore

Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD, Tel. +381 11 62 5344, Fax.+381 11 63 5777

Internet: http://www.semiconductors.philips.com

© Philips Electronics N.V. 1999

SCA 65

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

465008/01/pp20

Date of release: 1999 Jun 04

Document order number: 9397 750 05841

Let's make things better.

Philips

